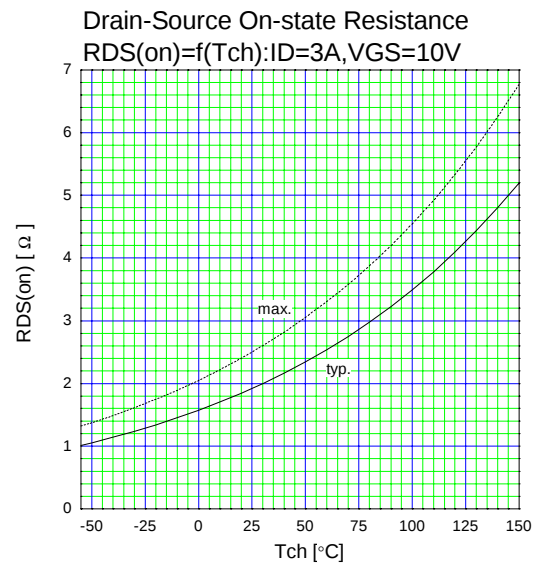
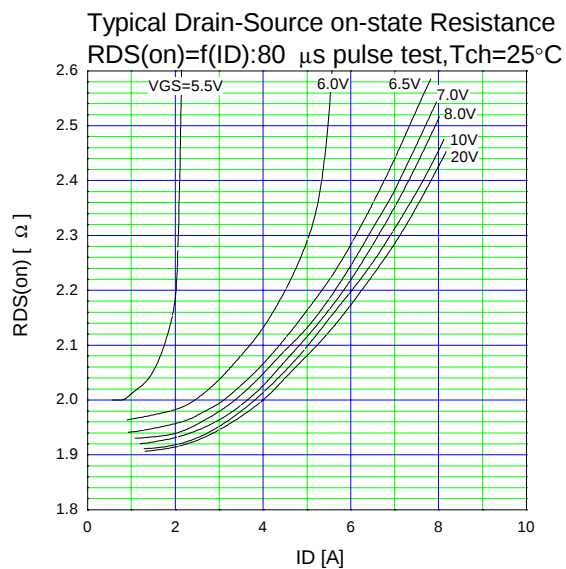
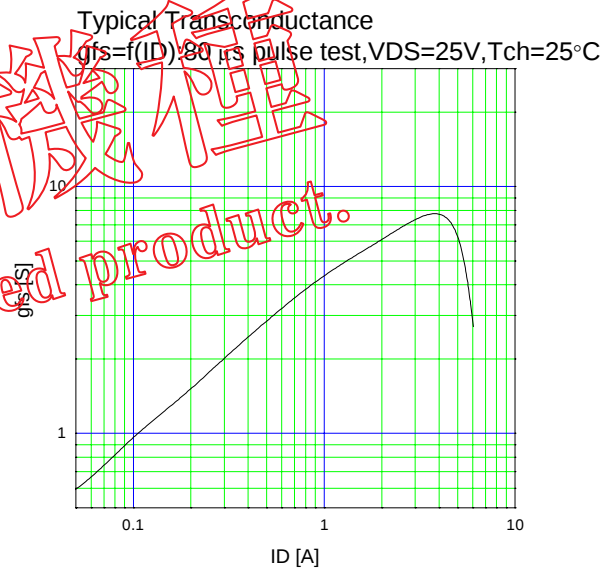
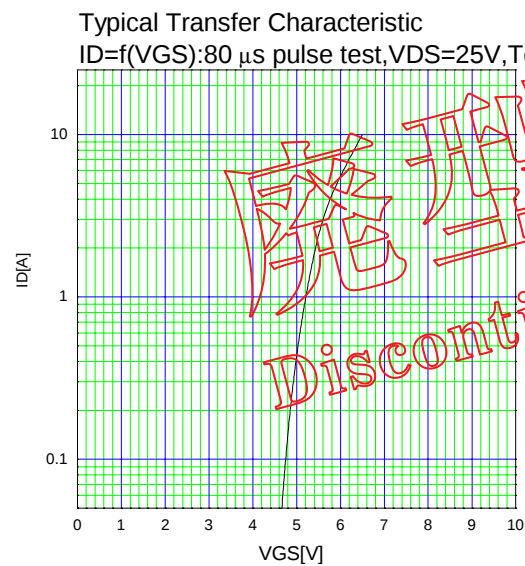
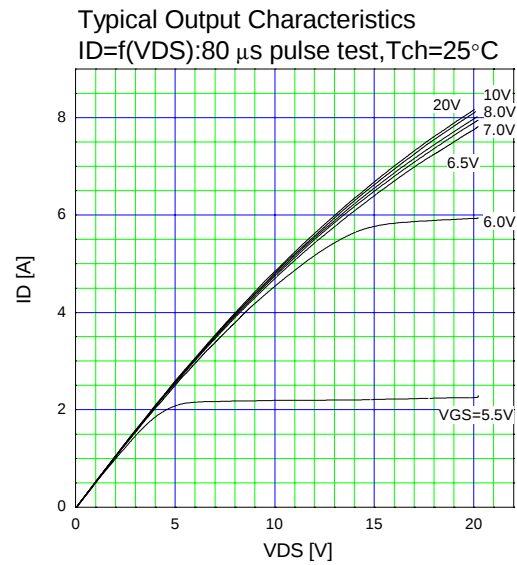
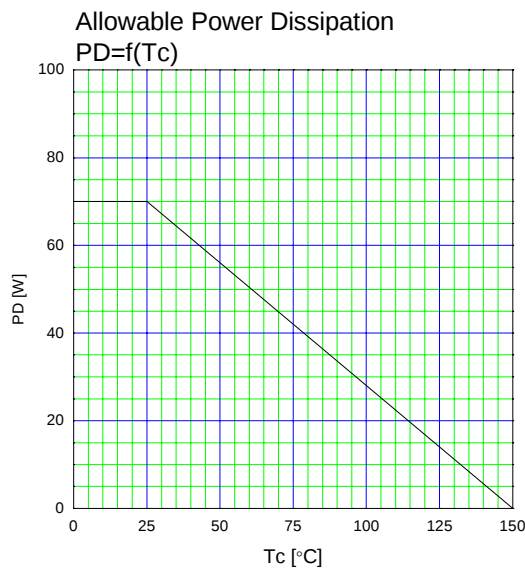
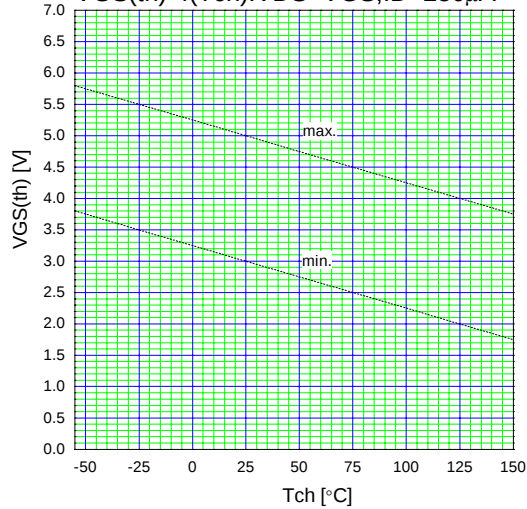


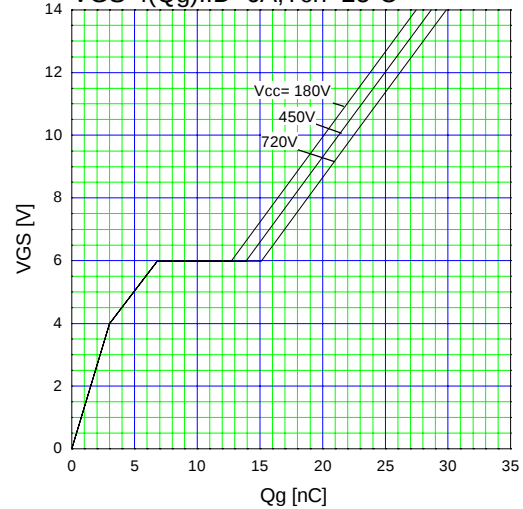
Characteristics



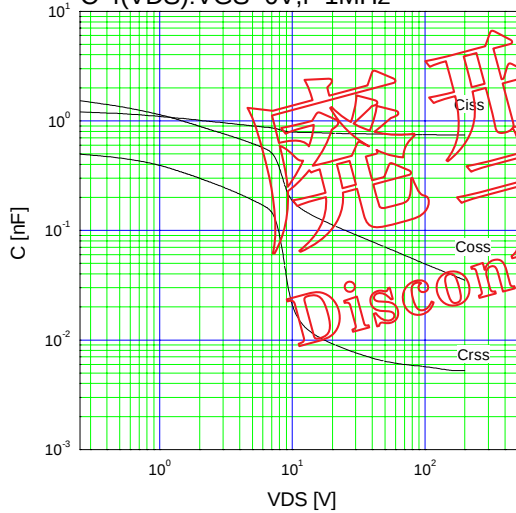
Gate Threshold Voltage vs. T_{ch}
 $V_{GS(th)} = f(T_{ch})$: $V_{DS} = V_{GS}$, $I_D = 250 \mu A$



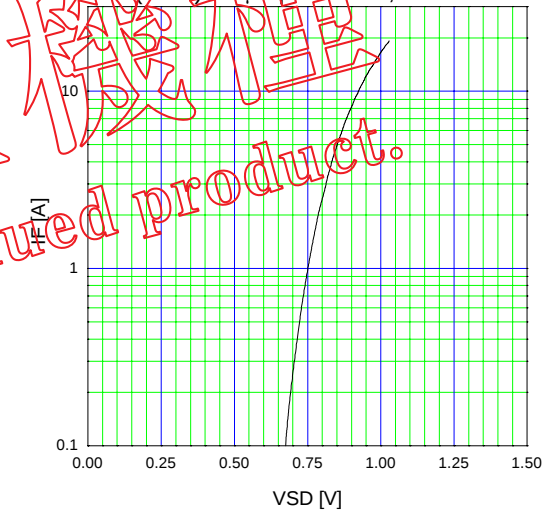
Typical Gate Charge Characteristics
 $V_{GS} = f(Q_g)$: $I_D = 6A$, $T_{ch} = 25^\circ C$



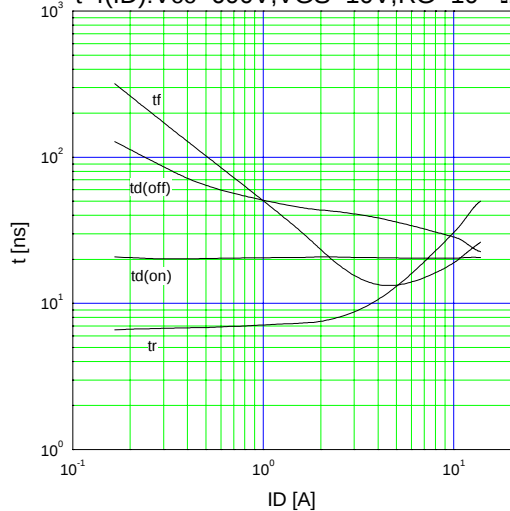
Typical Capacitance
 $C = f(V_{DS})$: $V_{GS} = 0V$, $f = 1MHz$



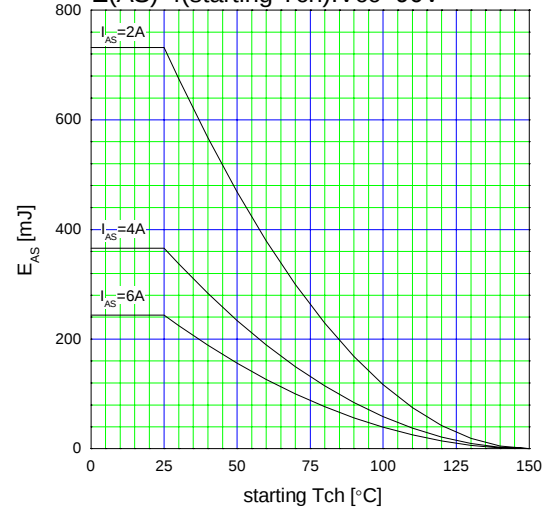
Typical Forward Characteristics of Reverse Diode
 $I_F = f(V_{SD})$: 80 μs pulse test, $T_{ch} = 25^\circ C$

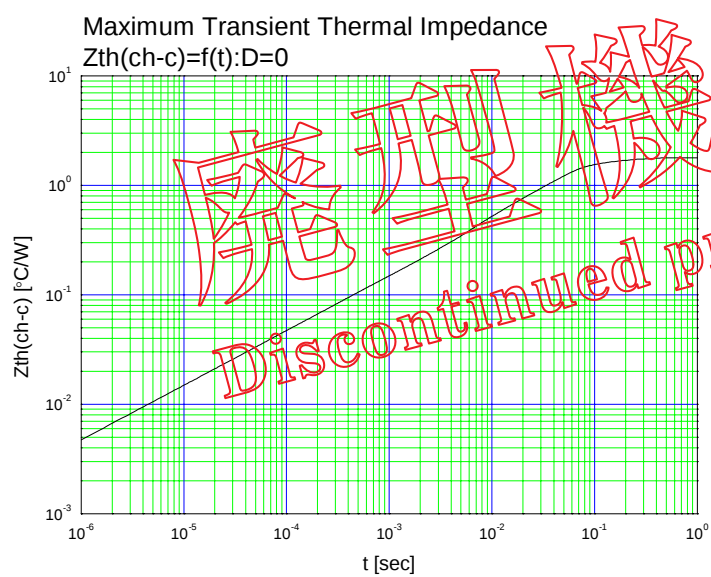
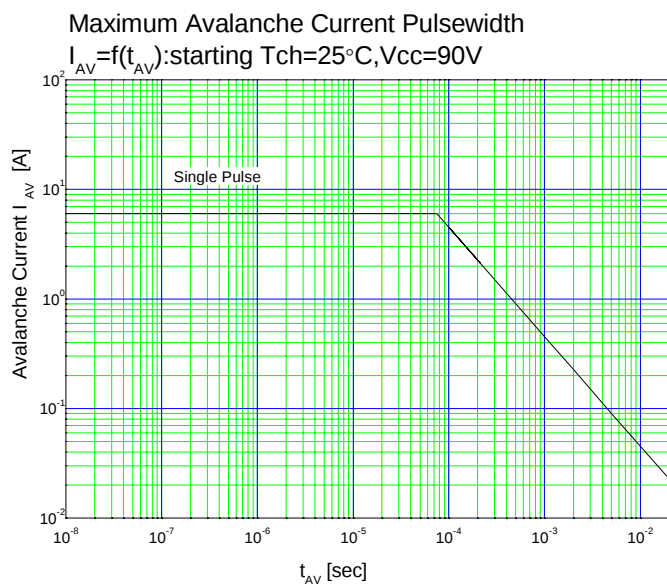


Typical Switching Characteristics vs. I_D
 $t = f(I_D)$: $V_{CC} = 600V$, $V_{GS} = 10V$, $R_G = 10 \Omega$



Maximum Avalanche Energy vs. starting T_{ch}
 $E_{AS} = f(\text{starting } T_{ch})$: $V_{CC} = 90V$





廃止機種
Discontinued product.